Bipolar Transistor

15 V, 0.7 A, Low V_{CE}(sat) NPN Single MCP

15C01M

Features

- Large Current Capacity
- Low Collector-to-Emitter Saturation Voltage (resistance) RCE (sat) typ.= 0.58Ω [I_C = 0.7 A, I_B = 35 mA]
- Ultrasmall Package Facilitates Miniaturization in end products
- Small ON-resistance (Ron)
- These Devices are Pb–Free and Halide Free

Applications

• Low-frequency Amplifier, muting circuit

Specifications

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V _{CBO}	Collector–to–Base Voltage		20	V
V _{CEO}	Collector–to–Emitter Voltage		15	V
V _{EBO}	Emitter-to-Base Volt- age		5	V
Ι _C	Collector Current		700	mA
I _{CP}	Collector Current (Pulse)		1.4	A
P _C	Collector Dissipation			

	Junction Temperature		150	°C
Tstg	Storage Temperature		–55 to +150	°C

assumed, damage may occur and reliability may be affected.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be

1 :Base

DATA SHEET

MARKING DIAGRAM

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ELECTRICAL	CHARACTERISTICS (T _A = 25°C)
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			Ratings			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	Collector Cutoff Current	V _{CB} = 15 V, I _E = 0 A	-	-	0.1	μΑ
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4 V I_C = 0 A$	-	-	0.1	μΑ
h _{FE}	DC Current Gain	$V_{CE} = 2 V, I_{C} = 10 mA$	300	-	800	-
f _T	Gain-Bandwidth Product	$V_{CE} = 2 V, I_{C} = 50 mA$	-	330	-	MHz
Cob	Output Capacitance	V _{CB} = 10 V, f = 1 MHz	-	3.2	-	pF
V _{CE} (sat)	Collector-to-Emitter Saturation Voltage	I _C = 200 mA, I _B = 10 mA	-	150	300	mV
V _{BE} (sat)	Base-to-Emitter Saturation Voltage	I _C = 200 mA, I _B = 10 mA	-	0.9	1.2	V
V _{(BR)CBO}	Collector-to-Base Breakdown Voltage	I _C = 10 μA, I _E = 0 A	20	-	-	V
V _{(BR)CEO}	Collector-to-Emitter Breakdown Voltage	$I_{C} = 1 \text{ mA}, R_{BE} = \infty$	15	-	-	V
V _{(BR)EBO}	Emitter-to-Base Breakdown Voltage	I _E = 10 μA, I _C = 0 A	5	-	-	V
t _{on}	Turn–On Time	See specified Test Circuit.	-	30	-	ns
t _{stg}	Storage Time		-	77	-	ns
t _f	Fall Time	1	-	40	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS







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TYPICAL CHARACTERISTICS (CONTINUED)

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